

Single Channel Silicon ESD Protector Overvoltage Protection Device

Specification Status: Preliminary

BENEFITS

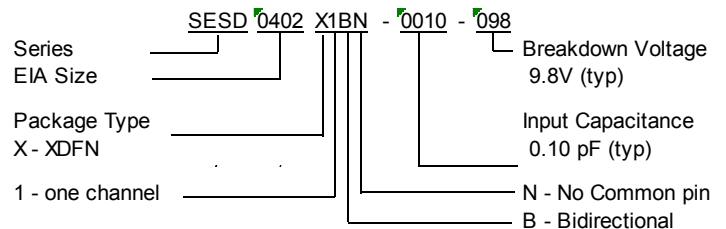
- Industry-leading lowest capacitance; provides lowest insertion loss for high speed data signals
- Small size ESD protection diodes for high speed data signals (0402 size devices)
- Helps protect electronic circuits against damage from Electrostatic Discharge (ESD), surge and cable discharge events
- Assists equipment to pass IEC61000-4-2, level 4 testing

FEATURES

- Low capacitance: 0.10 pF (typ, bi-di)
- Low leakage current: 50nA @ 5V (max)
- Low clamping voltage: $\pm 9.90V$ (typ, bi-di) @ (tp=8x20 μ s, Ipp=2A)
- ESD maximum rating per IEC61000-4-2 standard:
 - $\pm 20kV$ contact discharge
 - $\pm 20kV$ air discharge
- Surge: 2A (max, bi-di) @ (tp=8x20 μ s) per IEC61000-4-2-5
- Small size and low profile: XDFN packages
- Bi-directional operation



PART NUMBERING



APPLICATIONS

- Consumer, mobile and portable electronics
- Tablet PC and external storage with high speed interfaces
- Ultra-high speed data lines
- USB 3.0/2.0, HDMI 1.3/1.4, DisplayPort, Thunderbolt (Light Peak), V-by-One HS, and LVDS interfaces
- Applications requiring high ESD performance in small packages

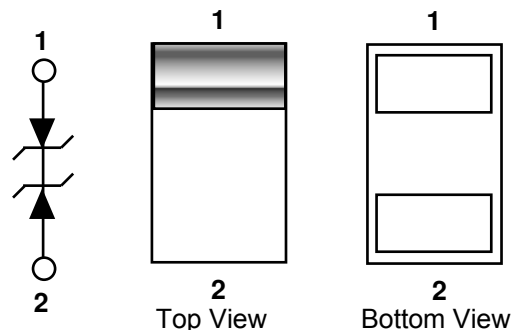
MATERIALS INFORMATION

RoHS Compliant ELV Compliant Halogen Free * Lead Free



* Halogen Free refers to: Br \leq 900ppm, Cl \leq 900ppm, Br+Cl \leq 1500ppm
SESD devices meet MSL-1 Requirements
DFN case epoxy meets UL 94 V-0

SCHEMATIC AND PIN CONFIGURATION



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DEVICE MAXIMUM RATING

ESD Withstand ⁽¹⁾ (IEC 61000-4-2, level 4)		Temperature		Peak Current (tp=8x20µs)
Contact (kV)	Air (kV)	Operating (°C)	Storage (°C)	I _{pp} (A)
± 20	± 20	-55 to +125	-55 to +150	2.0

⁽¹⁾ 20kV @ ± 1 pulse; 10kV @ ± 50 pulses; 8kV @ 1,000 pulses (under IEC6100-4-2)

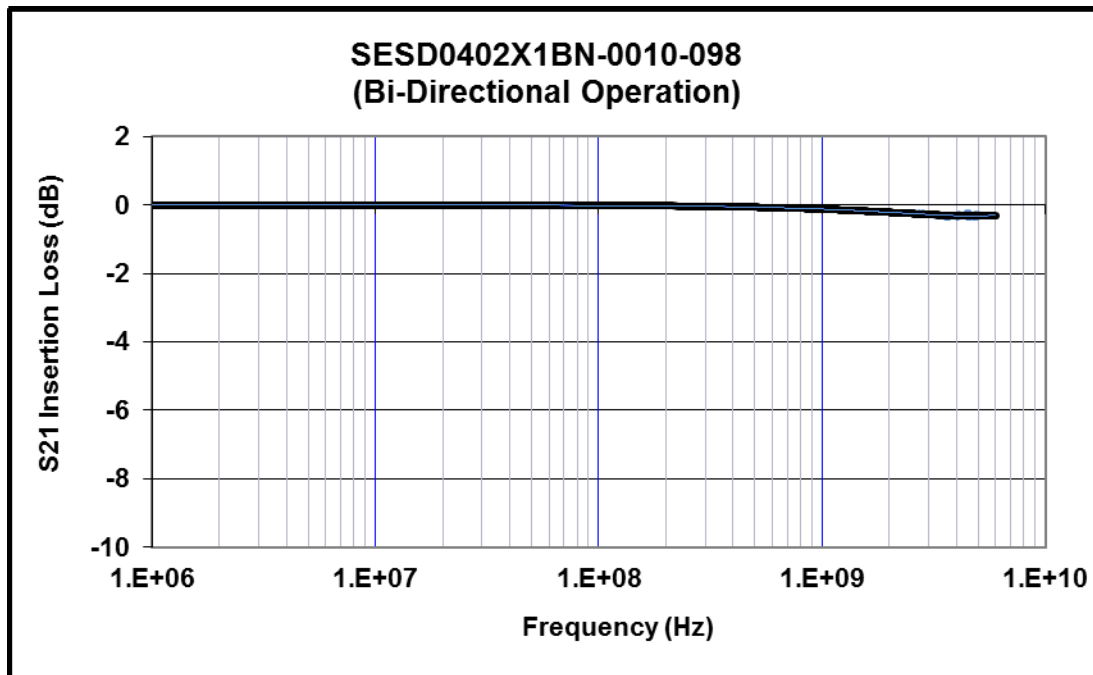
- Device maximum rating @ T = 25°C, unless otherwise specified
- Caution: Stress exceeding Device Maximum Ratings may damage the device
Prolonged exposure to stresses above the recommended operating conditions may affect device reliability

DEVICE ELECTRICAL CHARACTERISTICS

Input Capacitance @ V _R = 0V, f = 3GHz (pF)		Breakdown Voltage V _{BR} @ I _T =1mA (V)	Reverse Working Voltage (V)		Reverse Leakage Current I _L @ V _{WRV} =5.0V (nA)		Clamping Voltage V _{CL} @ I _{pp} =2.0A (V)
Typ	Maximum	Typ	Min	Max	Typ	Max	Max
0.10	0.12	+9.80 / -9.80	-9.00	+9.00	<5.0	50.0	+9.90 / -9.90

- All device electrical characteristics @ T = 25°C, unless otherwise specified

FIGURE 1. INSERTION LOSS DIAGRAM



Application	Bit Rate (Gbps)	@Freq (GHz)	Ins. Loss (dB)
HDMI 1.4 (1080P)	2.25	1.13	-0.12
DisplayPort	2.70	1.35	-0.16
HDMI 1.4 (max spec)	3.40	1.70	-0.19
USB3.0	5.00	2.50	-0.23
eSATA	6.00	3.00	-0.27
Thunderbolt	10.0	5.00	-0.30

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FIGURE 2. DEVICE IV CURVE

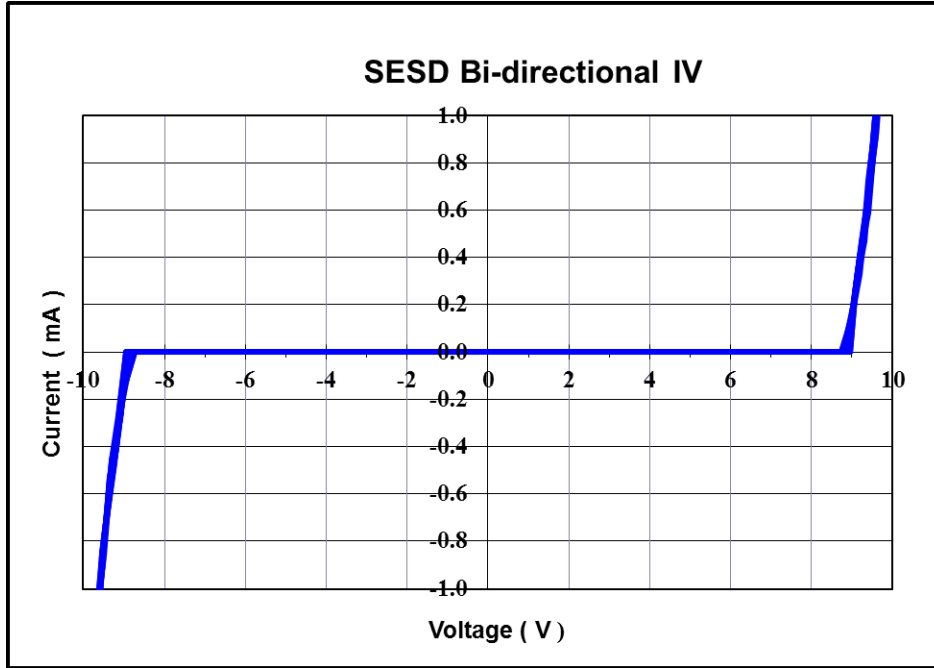
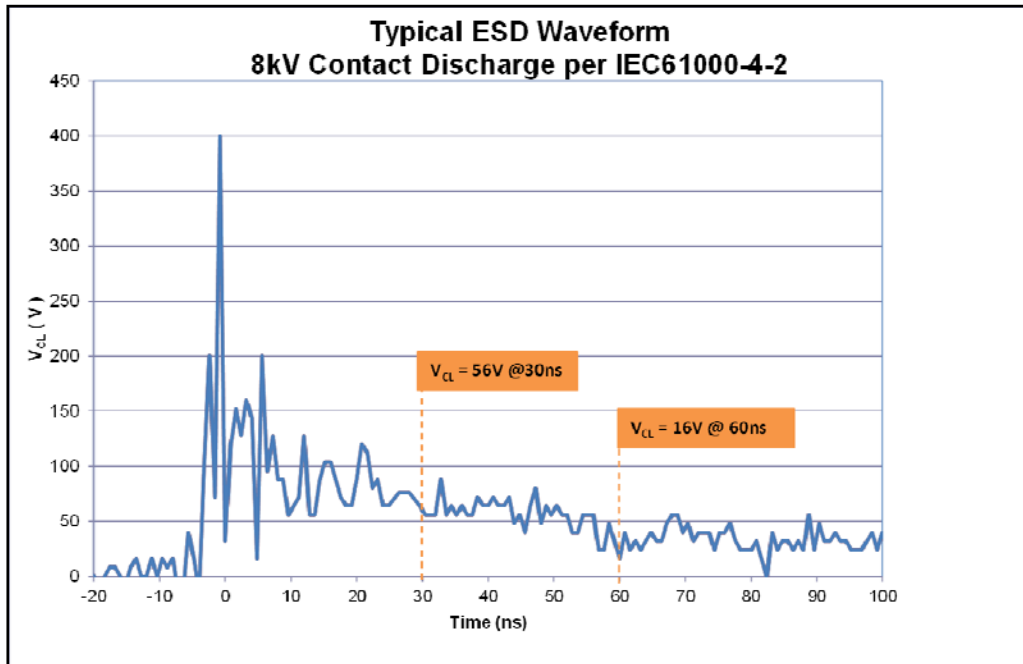
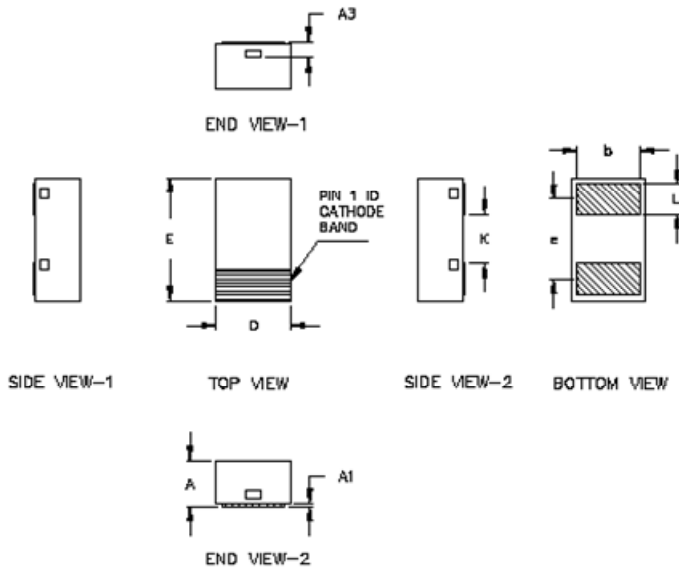


FIGURE 4. ESD WITHSTAND



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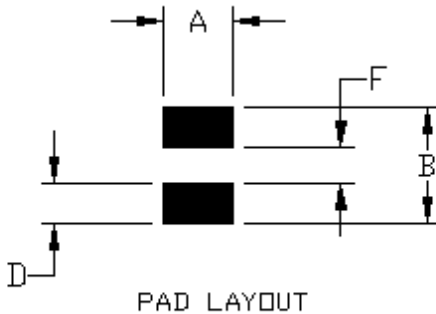
DEVICE DIMENSIONS



SESD0402X1BN-0010-098						
Dim	Millimeters (mm)			Inches (in)		
	Min	Nom	Max	Min	Nom	Max
A	0.33	0.38	0.43	0.0130	0.0150	0.0170
A1	0	-	0.05	0	-	0.0020
A3	0.130 ref.			0.005 ref.		
D	0.550	0.600	0.650	0.0220	0.0240	0.0260
E	0.950	1.000	1.050	0.0370	0.0390	0.0410
K	0.350	0.400	0.450	0.0140	0.0160	0.0180
b	0.450	0.500	0.550	0.0180	0.0200	0.0220
L	0.200	0.250	0.300	0.0080	0.0100	0.0120
e	0.650 BSC			0.026 BSC		

BSC – Basic Spacing between Centers

RECOMMENDED LANDING PATTERN:



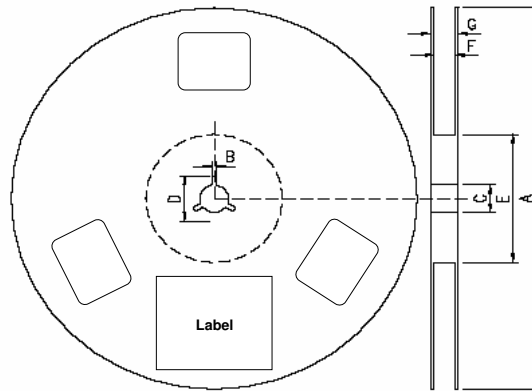
SESD Landing Pad Layout 0402 Package		
Symbol	Millimeters (mm)	Inches (in)
A	0.60	0.024
B	1.00	0.039
D	0.35	0.014
F	0.30	0.012

PACKAGING

Packaging	Tape & Reel	Standard Box
SESD0402X1BN-0010-098	10,000	50,000

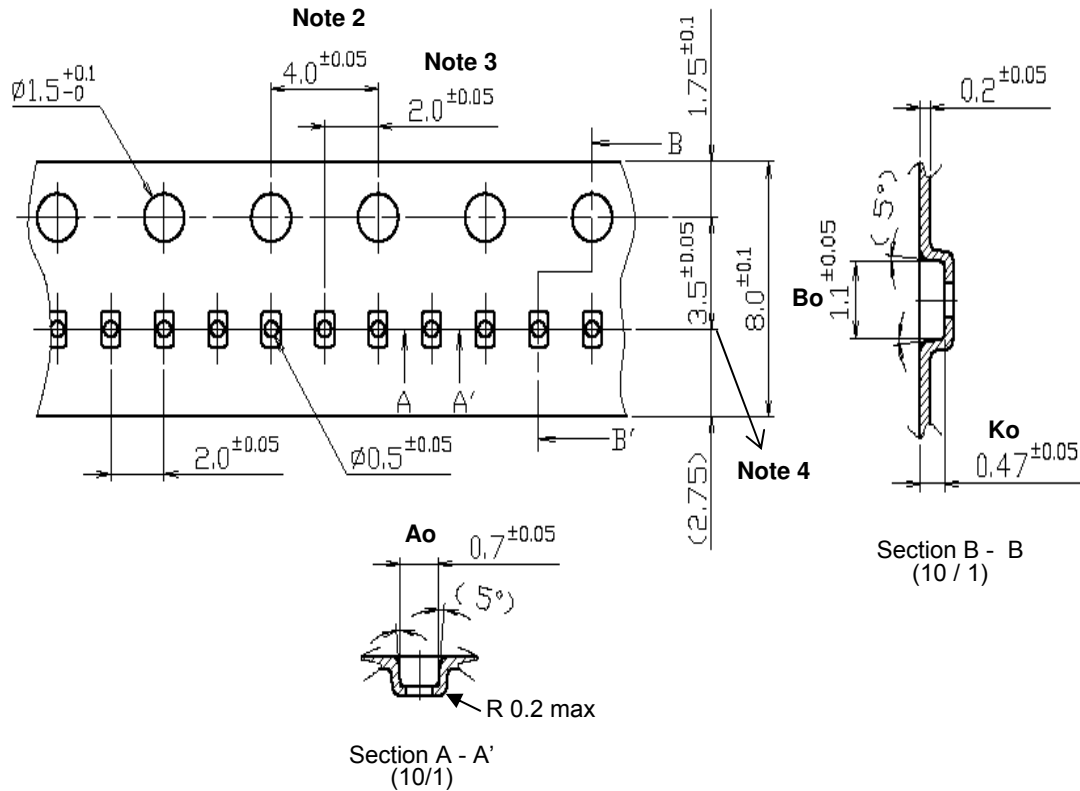
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REEL DIMENSIONS



Dimensions	A	B	C	D	E	F	G
(mm)	180.0 ± 1.5	2.3. 0 ± 0.2	13.0 + 0.5 / -0.2	17.3 ± 0.2	60.5 ± 1.5	8.4 + 1.5/-0.0	14.4 (max)

CARRIER TAPE DIMENSIONS



Ao	0.07 ± 0.05
Bo	1.10 ± 0.05
Ko	0.47 ± 0.05

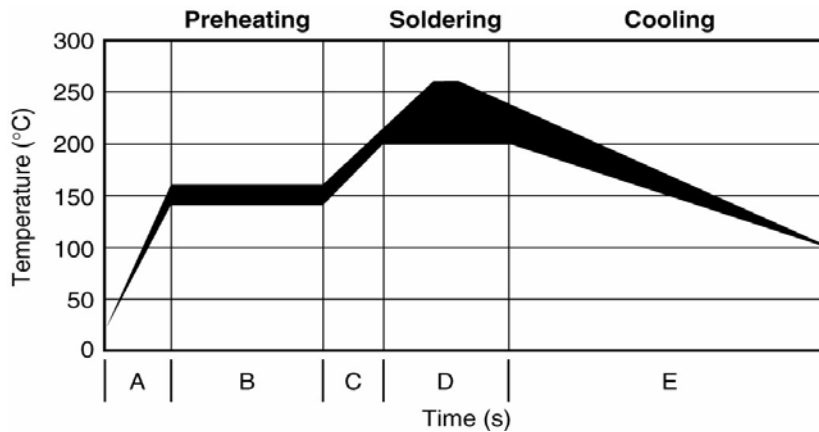
Note 1. All dimensions in mm
 Note 2. Cumulative tolerance is 200 ± 0.3 / 50MM pitch
 Note 3. Center point of hole tolerance is 2.0 ± 0.5
 Note 4. Center point of hole tolerance is 3.5 ± 0.5

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SOLDER REFLOW RECOMMENDATION

A	Temperature ramp up 1	From ambient to Preheating temperature	30s to 60s
B	Preheating	140°C - 160°C	60s to 120s
C	Temperature ramp up 2	From Preheating to Main heating temperature	20s to 40s
D	Main heating	at 200°C at 220°C at 240°C at 260°C	60s ~ 70s 50s ~ 60s 30s ~ 40s 5s ~ 10s
E	Cooling	From main heating temperature to 100°C	4°C/s (max)

FIGURE 4. REFLOW PROFILE



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